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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

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SEMICONDUCTOR®

December 2013

FQP6N40C

N-Channel QFET[®] MOSFET

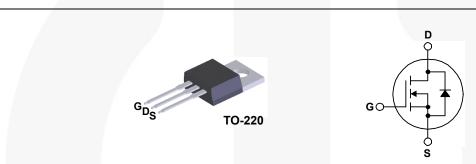
400 V, 6.0 A, 1.0 Ω

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 6.0 A, 400 V, $R_{DS(on)}$ = 1.0 Ω (Max.) @ V_{GS} = 10 V, I_D = 3 A
- Low Gate Charge (Typ. 16 nC)
- Low Crss (Typ. 15 pF)
- 100% Avalanche Tested



Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

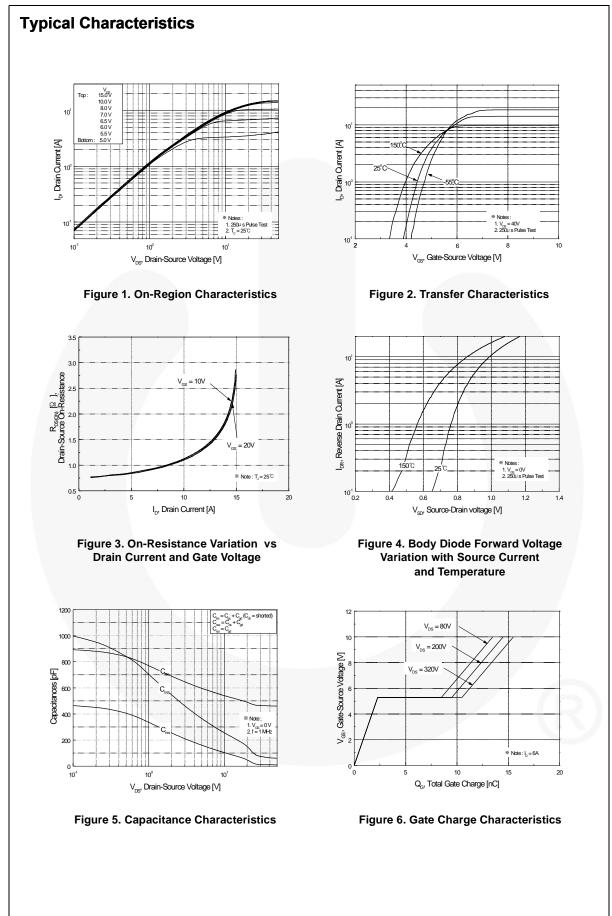
Symbol	Parameter	FQP6N40C	Unit		
V _{DSS}	Drain-Source Voltage		400	V	
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		6	А	
	- Continuous (T _C = 100°C)		3.6	A	
I _{DM}	Drain Current - Pulsed	(Note 1)	24	A	
V _{GSS}	Gate-Source Voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	270	mJ	
I _{AR}	Avalanche Current	(Note 1)	6	A	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	7.3	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns	
P _D	Power Dissipation ($T_C = 25^{\circ}C$)		73	W	
	- Derate above 25°C		0.58	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.		300	°C	

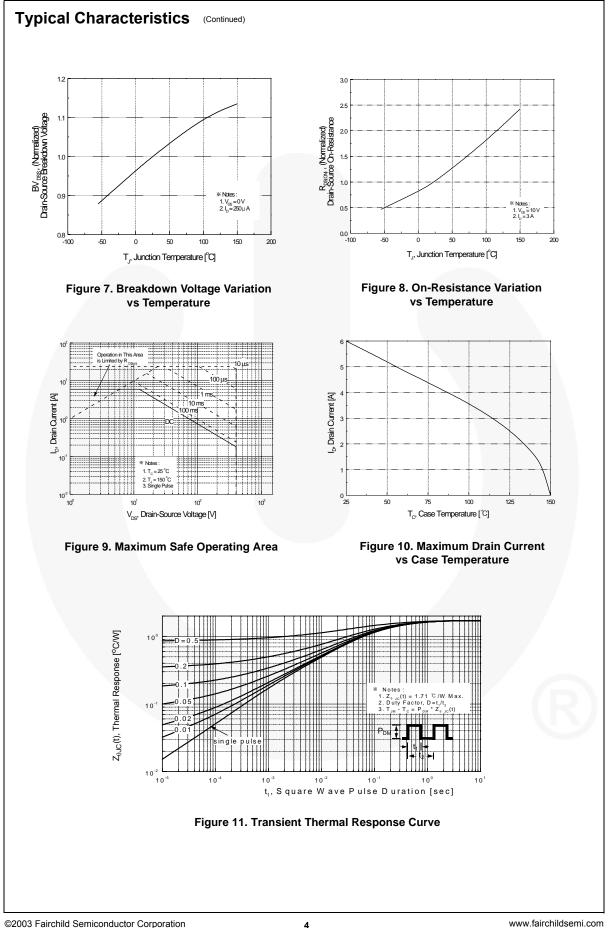
Thermal Characteristics

Symbol	Parameter	FQP6N40C	Unit	
R _{θJC}	Thermal Resistance, Junction-to-Case, Max.	1.71	°C/W	
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

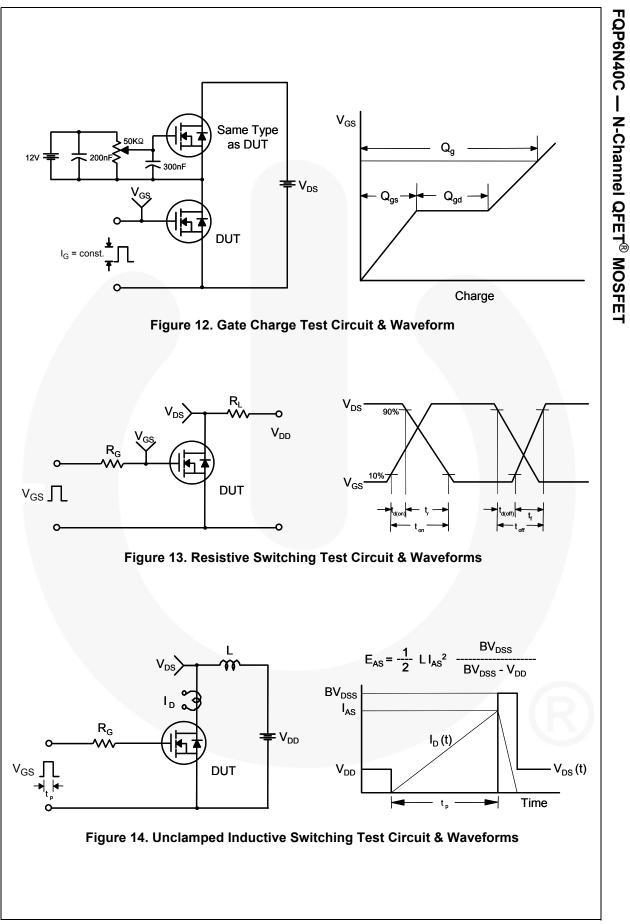
Part Number FQP6N40C		Top Mark Pac		kage Packing Method Reel		Size	Tape Width		Quantity	
		FQP6N40C	TO-	220 Tube		N/A		N/A		50 units
lectrio	cal Cha	racteristics	To = 25°0	Cunless off	nerwise noted.					
Symbol		Parameter	6		Test Conditions		Min.	Тур.	Max.	Unit
Off Cha	aracterist	ice							,	,
BV _{DSS}	Drain-Source Breakdown Voltage		V _{GS} =	0 V, I _D = 250 μA		400			V	
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient		$I_D = 250 \mu$ A, Referenced to 25°C				0.54		V/°C	
DSS	Zero Gate Voltage Drain Current		ont	V _{DS} = 400 V, V _{GS} = 0 V					1	μA
		-		$V_{DS} = 320 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$					10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward			30 V, V _{DS} = 0 V				100	nA	
I _{GSSR}	Gate-Bod	Gate-Body Leakage Current, Reverse		$V_{GS} =$	-30 V, $V_{DS} = 0 V$				-100	nA
On Cha	aracterist	ics								
V _{GS(th)}	Gate Thre	eshold Voltage		$V_{DS} =$	V _{GS} , I _D = 250 μA	- /	2.0		4.0	V
R _{DS(on)}	Static Dra On-Resist	in-Source tance		V _{GS} = 10 V, I _D = 3A				0.83	1	Ω
9fs	Forward 7	Transconductance		$V_{DS} =$	40 V, I _D = 3A			4.7		S
Dvnami	ic Chara	cteristics								
C _{iss}	Input Cap		_	Vpg =	25 V, V _{GS} = 0 V,			480	625	pF
C _{oss}	Output Ca	apacitance		f = 1.0				80	105	pF
C _{rss}	Reverse	Reverse Transfer Capacitance						15	20	pF
Switchi	ing Char									
t _{d(on)}		acteristics Delay Time	-					13	35	ns
t _r	Turn-On F		_		00 V, $I_D = 6A$,			65	140	ns
d(off)		Delay Time	_	R _G = 2	5 Ω			21	55	ns
f	Turn-Off F			-		(Note 4)		38	85	ns
Q _g	Total Gate	e Charge		Vpc =	320 V, I _D = 6A,			16	20	nC
Q _{gs}		rce Charge		$V_{GS} =$				2.3		nC
Q _{gd}	Gate-Drai	ů,		. 62		(Note 4)		8.2		nC
Ducin O										
Drain-S	1	ode Character			•	- /			6	A
SM		aximum Pulsed Drain-Source Diode F							24	A
V _{SD}		Source Diode Forward Voltage		$V_{GS} = 0 \text{ V}, \text{ I}_{S} = 6 \text{ A}$					1.4	V
t _{rr}		Recovery Time			$0 \text{ V}, \text{ I}_{\text{S}} = 6 \text{ A},$			230		ns
Q _{rr}		Recovery Charge		$dI_{\rm F} / dt = 100 \text{ A/}\mu\text{s}$			1.7		μC	
							1			Ŕ
		dth limited by maximum ju _{DD} = 50 V, R _G = 25 Ω, star	ting T _J = 25°							

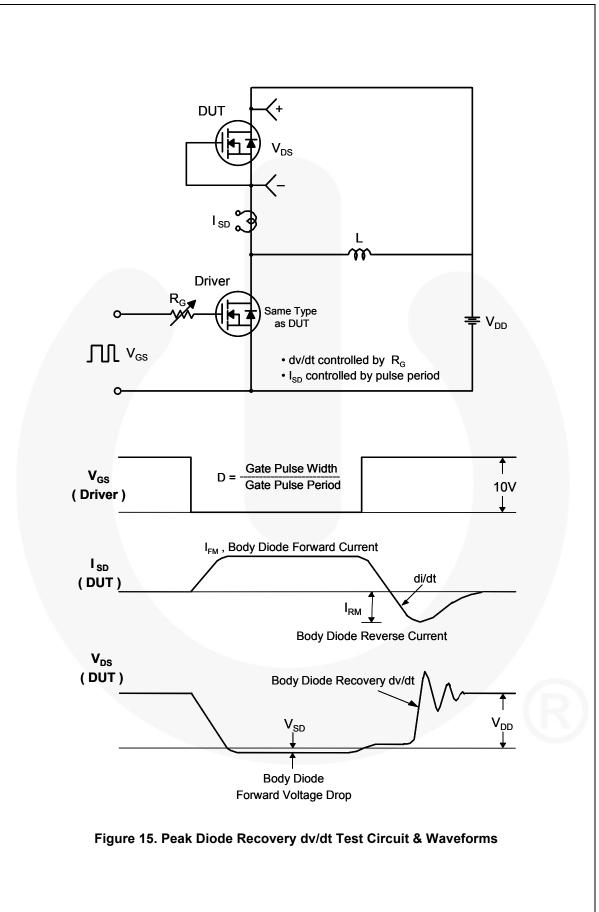
FQP6N40C — N-Channel QFET[®] MOSFET

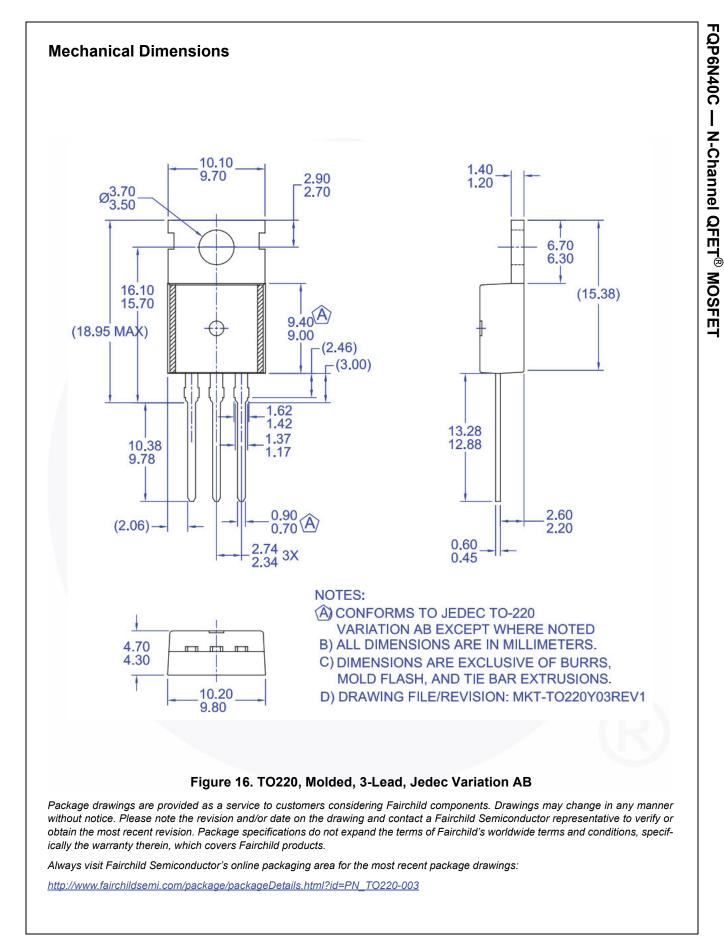




FQP6N40C — N-Channel QFET[®] MOSFET









Rev. 166

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